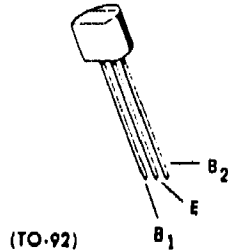


2N4870 (SILICON)
2N4871



PN unijunction transistors designed for use in pulse and timing circuits, sensing circuits and thyristor trigger circuits.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
RMS Power Dissipation*	P_D^*	300	mW
RMS Emitter Current	I_e	50	mA
Peak-Pulse Emitter Current**	i_e^{**}	1.5	Amp
Emitter Reverse Voltage	V_{B2E}	30	Volts
Interbase Voltage†	V_{B2B1}^\dagger	35	Volts
Operating Junction Temperature Range	T_J	-65 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Characteristic	Symbol	Min	Typ	Max	Unit
Intrinsic Standoff Ratio* ($V_{B2B1} = 10\text{ V}$)	n	0.56 0.70	-	0.75 0.85	
Interbase Resistance ($V_{B2B1} = 3.0\text{ V}$, $I_E = 0$)	R_{BB}	4.0	6.0	9.1	k ohms
Interbase Resistance Temperature Coefficient ($V_{B2B1} = 3.0\text{ V}$, $I_E = 0$, $T_A = -65$ to $+125^\circ\text{C}$)	αR_{BB}	0.10	-	0.90	$\% / ^\circ\text{C}$
Emitter Saturation Voltage** ($V_{B2B1} = 10\text{ V}$, $I_E = 50\text{ mA}$)	$V_{EB1(\text{sat})}^{**}$	-	2.5	-	Volts
Modulated Interbase Current ($V_{B2B1} = 10\text{ V}$, $I_E = 50\text{ mA}$)	$I_{B2(\text{mod})}$	-	15	-	mA
Emitter Reverse Current ($V_{B2E} = 30\text{ V}$, $I_{B1} = 0$)	I_{EB20}	-	0.005	1.0	μA
Peak-Point Emitter Current ($V_{B2B1} = 25\text{ V}$)	I_p	-	1.0	5.0	μA
Valley-Point Current** ($V_{B2B1} = 20\text{ V}$, $R_{B2} = 100\text{ ohms}$)	I_V^{**}	2.0 4.0	5.0 7.0	-	mA
Base-One Peak Pulse Voltage	V_{OB1}	3.0 5.0	6.0 8.0	-	Volts

